

## Dual N-Channel 20-V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
20	0.009 at $V_{GS} = 4.5$ V	10	15 nC
	0.012 at $V_{GS} = 2.5$ V	8.0	

### FEATURES

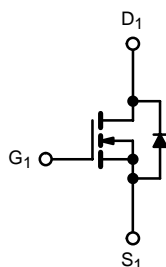
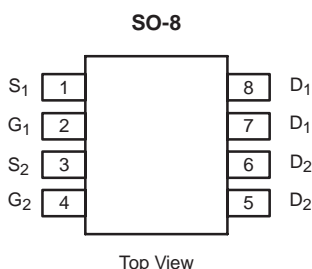
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % UIS Tested
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



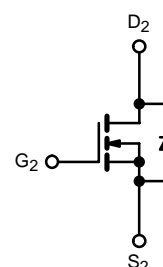
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Set Top Box
- Low Current DC/DC



N-Channel MOSFET



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current ( $T_J = 150$ °C)	$T_C = 25$ °C	10 <sup>a</sup>	A
	$T_C = 70$ °C	7.0	
	$T_A = 25$ °C	8.1 <sup>b, c</sup>	
	$T_A = 70$ °C	7.2 <sup>b, c</sup>	
Pulsed Drain Current	$I_{DM}$	44	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	3.25	
	$T_A = 25$ °C	1.88 <sup>b, c</sup>	
Single Pulse Avalanche Current	$I_{AS}$	6	mJ
Single Pulse Avalanche Energy	$E_{AS}$	1.45	
Maximum Power Dissipation	$T_C = 25$ °C	2.7	W
	$T_C = 70$ °C	1.77	
	$T_A = 25$ °C	1.78 <sup>b, c</sup>	
	$T_A = 70$ °C	1.14 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, c, d</sup>	$t \leq 10$ s	$R_{thJA}$	58	70	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	38	45	

Notes:

a. Package limited,  $T_C = 25$  °C.

b. Surface Mounted on 1" x 1" FR4 board.

c.  $t = 10$  s.

d. Maximum under Steady State conditions is 110 °C/W.

SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA		32		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			- 5.0		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.5		1.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 4.5 V	10			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V I <sub>D</sub> = 5 A		0.009		Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 4 A		0.012		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5 A		16		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0 V, f = 1 MHz		586		pF
Output Capacitance	C <sub>oss</sub>			117		
Reverse Transfer Capacitance	C <sub>rss</sub>			55		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		15		nC
		V <sub>DS</sub> = 10V , V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A		3.7	5.6	
Gate-Source Charge	Q <sub>gs</sub>			1.4		
Gate-Drain Charge	Q <sub>gd</sub>			1.05		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.8	4.3	8.6	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω		12	24	ns
Rise Time	t <sub>r</sub>			55	100	
Turn-Off Delay Time	t <sub>d(off)</sub>			11	22	
Fall Time	t <sub>f</sub>			8	16	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		4	8	
Rise Time	t <sub>r</sub>			9	18	
Turn-Off Delay Time	t <sub>d(off)</sub>			10	20	
Fall Time	t <sub>f</sub>			6	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			2.35	A
Pulse Diode Forward Current	I <sub>SM</sub>				24	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 2 A, V <sub>GS</sub> = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 5 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C		11	20	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			4	8	nC
Reverse Recovery Fall Time	t <sub>a</sub>			7		ns
Reverse Recovery Rise Time	t <sub>b</sub>			4		

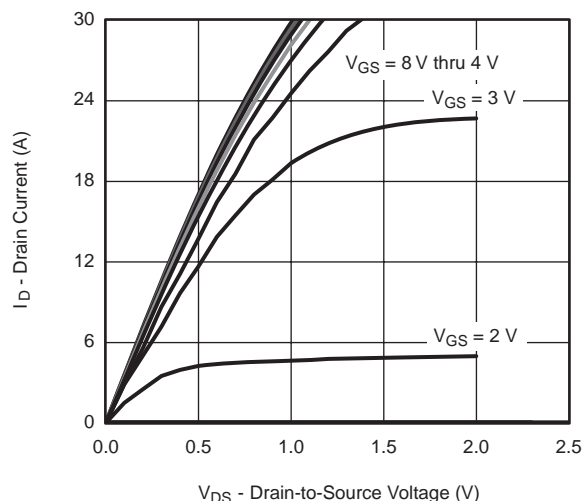
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ 

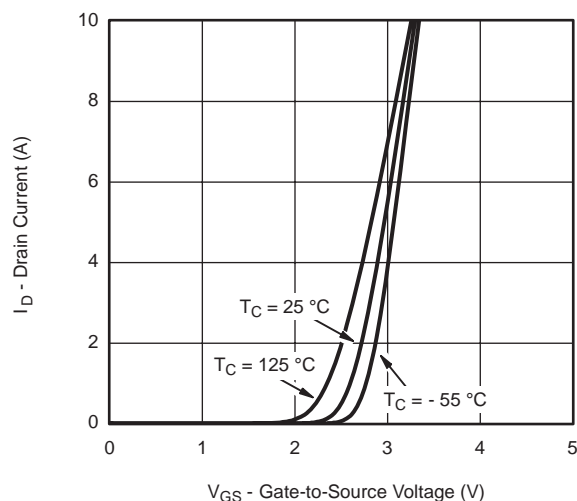
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

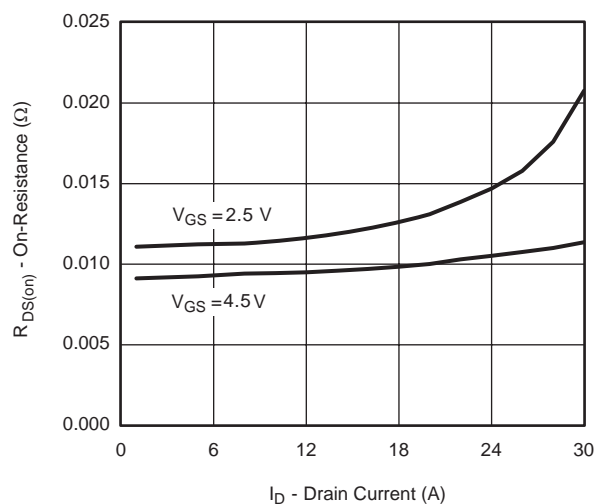
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



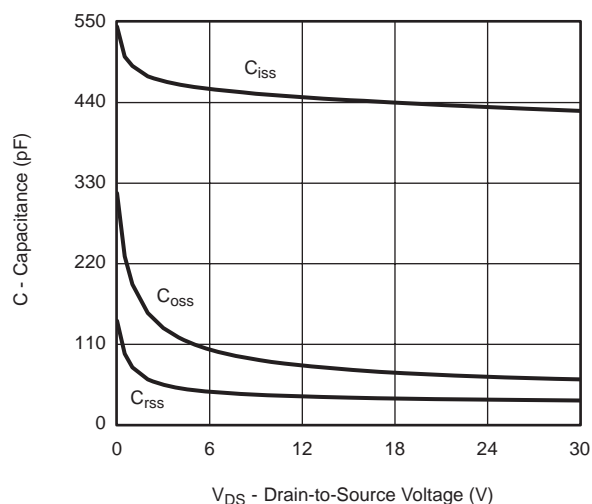
**Output Characteristics**



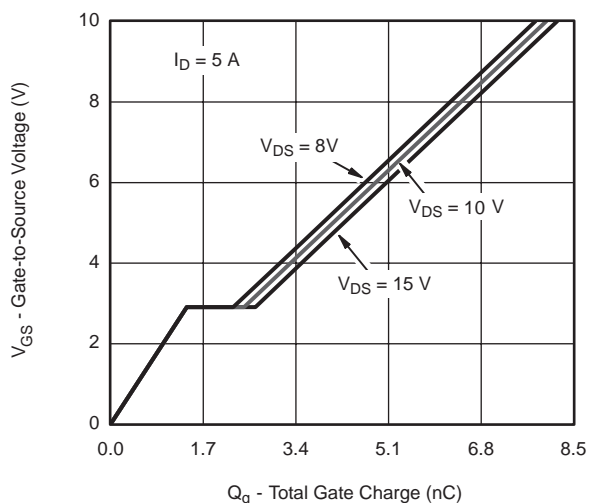
**Transfer Characteristics**



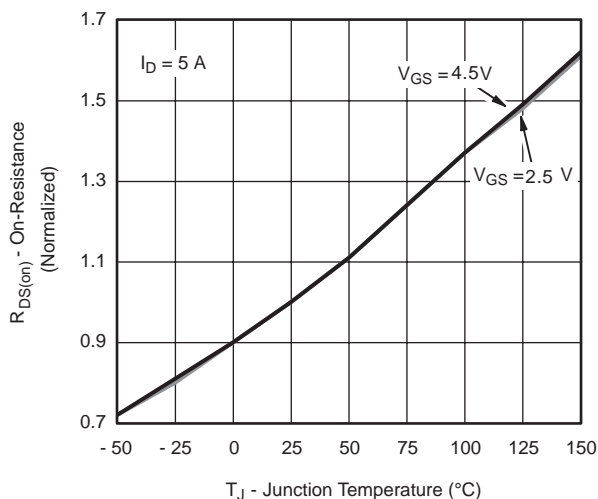
**On-Resistance vs. Drain Current**



**Capacitance**

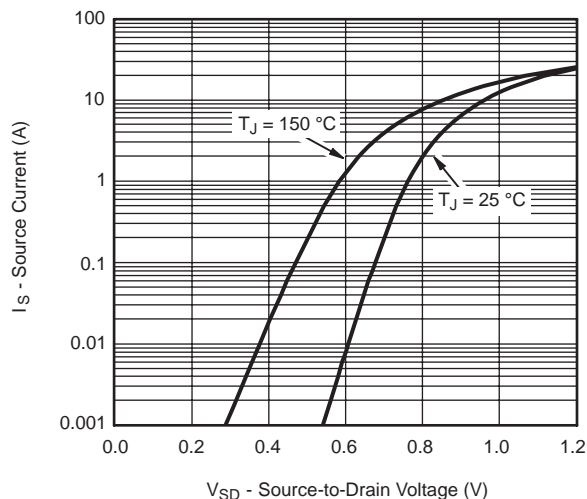


**Gate Charge**

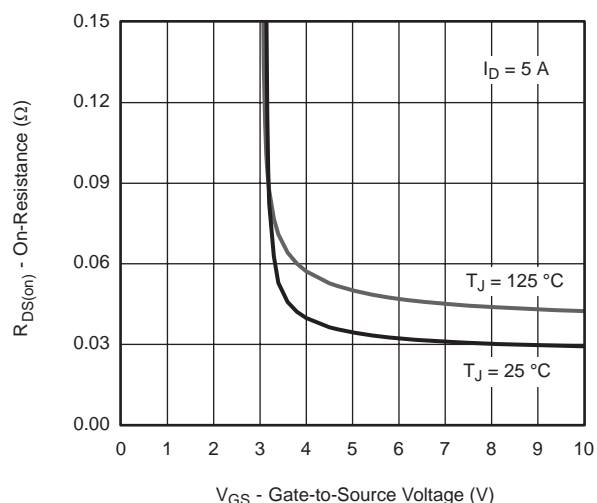


**On-Resistance vs. Junction Temperature**

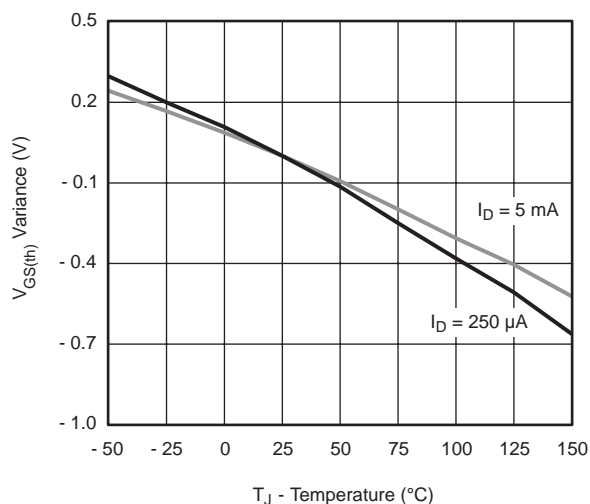
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



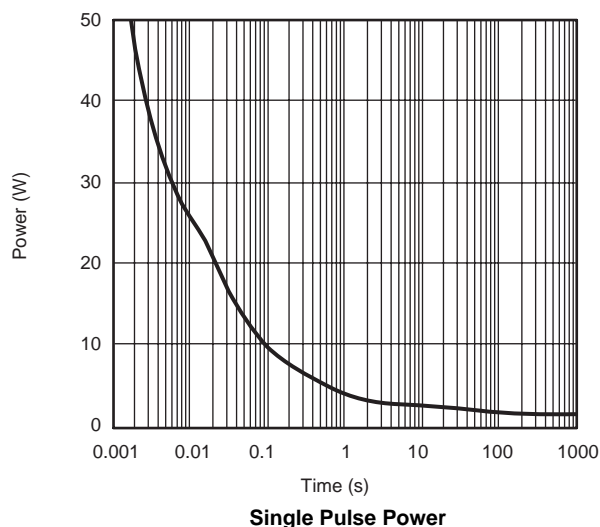
Source-Drain Diode Forward Voltage



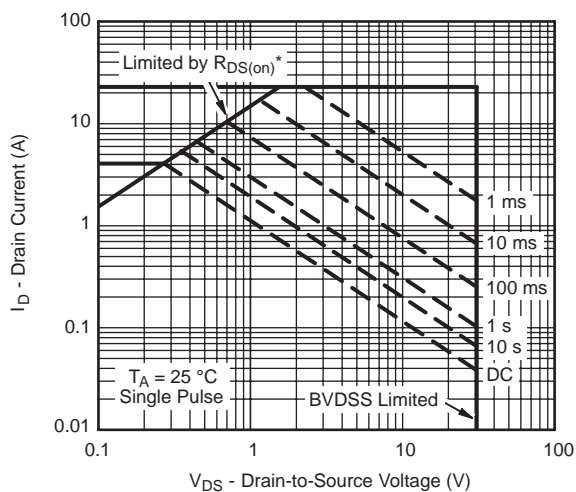
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

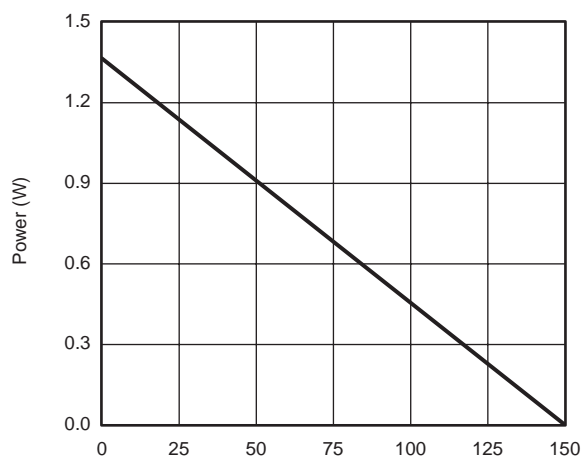
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



$T_C$  - Case Temperature (°C)  
**Current Derating\***



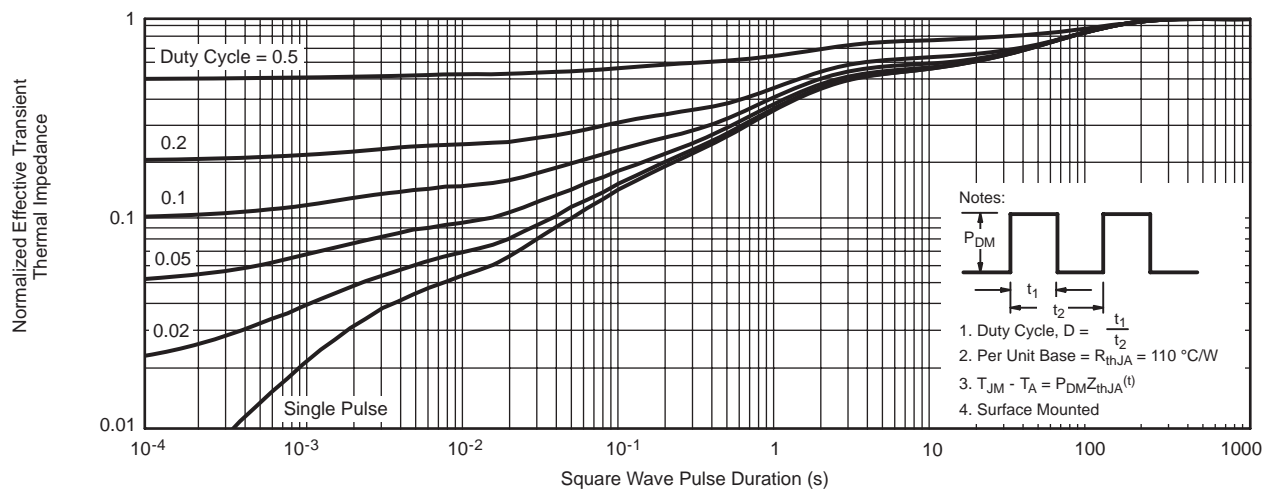
$T_C$  - Case Temperature (°C)  
**Power, Junction-to-Foot**



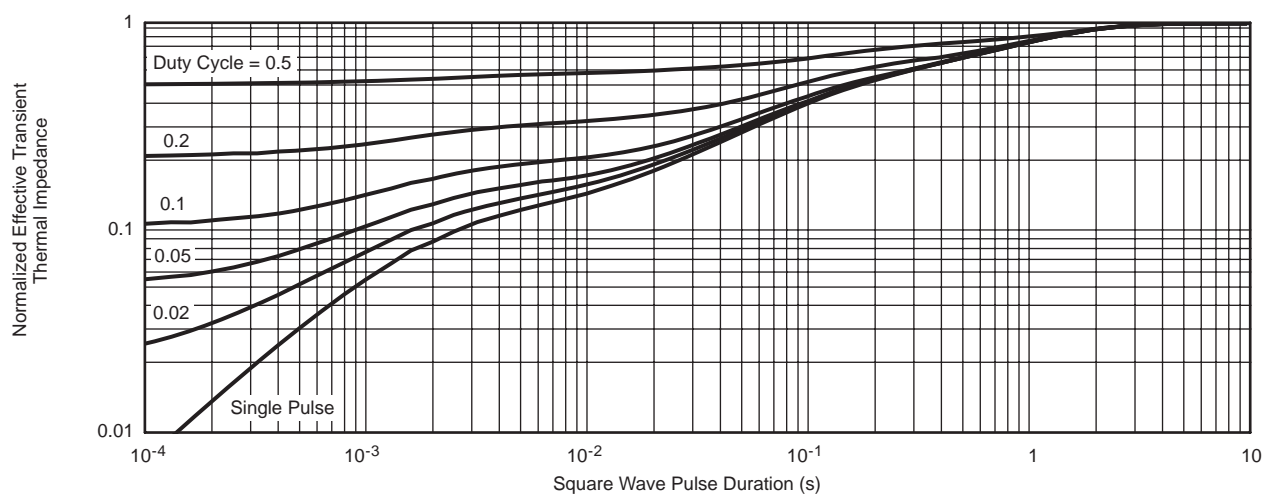
$T_A$  - Ambient Temperature (°C)  
**Power, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



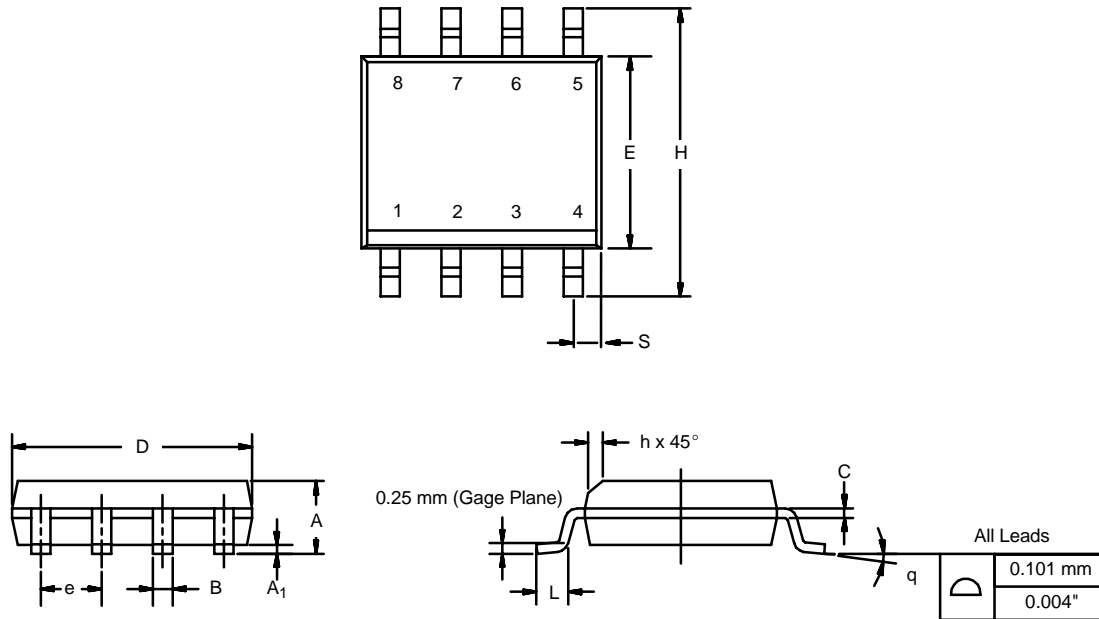
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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